

**FAIRCHILD**  
SEMICONDUCTOR®

**IGBT**

## FMS7G20US60

### Compact & Complex Module

#### General Description

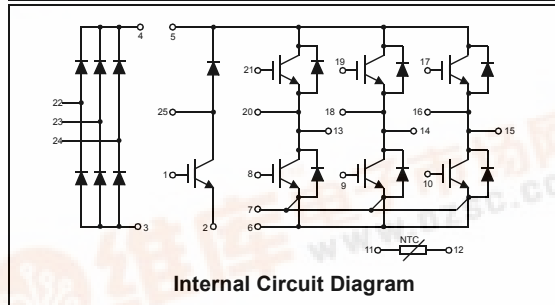
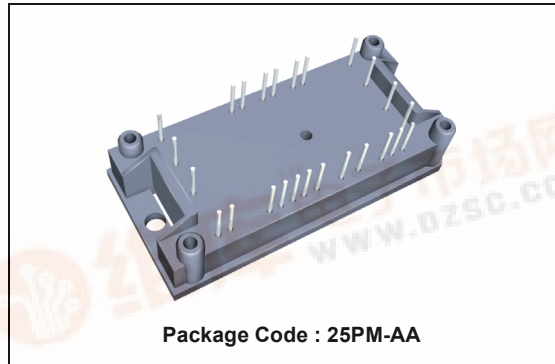
Fairchild IGBT Power Module provides low conduction and switching losses as well as short circuit ruggedness. It's designed for the applications such as motor control and general inverters where short-circuit ruggedness is required.

#### Features

- Short Circuit rated 10us @  $T_C = 100^\circ\text{C}$ ,  $V_{GE} = 15\text{V}$
- High Speed Switching
- Low Saturation Voltage :  $V_{CE(sat)} = 2.1\text{V}$  @  $I_C = 20\text{A}$
- High Input Impedance
- Built in Brake & 3 Phase Rectifier Circuit
- Fast & Soft Anti-Parallel FWD
- Built-in NTC Thermistor

#### Application

- AC & DC Motor Controls
- General Purpose Inverters
- Robotics
- Servo Controls



#### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

	Symbol	Description	FMS7G20US60	Units
Inverter & Brake	$V_{CES}$	Collector-Emitter Voltage	600	V
	$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
	$I_C$	Collector Current @ $T_C = 80^\circ\text{C}$	20	A
	$I_{CM(1)}$	Pulsed Collector Current	40	A
	$I_F$	Diode Continuous Forward Current @ $T_C = 80^\circ\text{C}$	20	A
	$I_{FM}$	Diode Maximum Forward Current	40	A
	$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	89	W
Converter	$T_{SC}$	Short Circuit Withstand Time @ $T_C = 100^\circ\text{C}$	10	us
	$V_{RRM}$	Repetitive Peak Reverse Voltage	1600	V
	$I_O$	Average Output Rectified Current	20	A
	$I_{FSM}$	Surge Forward Current @ 1Cycle at 60Hz, Peak value Non-Repetitive	200	A
Common	$i^2t$	Energy pulse @ 1Cycle at 60Hz	164	$\text{A}^2\text{s}$
	$T_J$	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
	$T_{STG}$	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
	$V_{ISO}$	Isolation Voltage @ AC 1minute	2500	V
Mounting Torque		Mounting part Screw @ M4	2.0	N.m

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature



### Electrical Characteristics of IGBT @ Inverter & Brake T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA	600	--	--	V
ΔB <sub>VCES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1mA	--	0.6	--	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	--	--	250	μA
I <sub>GES</sub>	Gate - Emitter Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V	--	--	± 100	nA
<b>On Characteristics</b>						
V <sub>GE(th)</sub>	Gate - Emitter Threshold Voltage	I <sub>C</sub> = 20mA, V <sub>CE</sub> = V <sub>GE</sub>	5.0	6.5	8.5	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 20A, V <sub>GE</sub> = 15V	--	2.1	2.7	V
<b>Dynamic Characteristics</b>						
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V, f = 1MHz	--	1277	--	pF
C <sub>oes</sub>	Output Capacitance		--	98	--	pF
C <sub>res</sub>	Reverse Transfer Capacitance		--	21	--	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 300 V, I <sub>C</sub> = 20A, R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 15V, Inductive Load, T <sub>C</sub> = 25°C	--	65	130	ns
t <sub>r</sub>	Rise Time		--	100	200	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	80	160	ns
t <sub>f</sub>	Fall Time		--	100	200	ns
E <sub>on</sub>	Turn-On Switching Loss		--	0.45	--	mJ
E <sub>off</sub>	Turn-Off Switching Loss		--	0.42	--	mJ
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 300 V, I <sub>C</sub> = 20A, R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 15V, Inductive Load, T <sub>C</sub> = 125°C	--	70	140	ns
t <sub>r</sub>	Rise Time		--	100	200	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	110	220	ns
t <sub>f</sub>	Fall Time		--	210	350	ns
E <sub>on</sub>	Turn-On Switching Loss		--	0.5	--	mJ
E <sub>off</sub>	Turn-Off Switching Loss		--	0.72	--	mJ
T <sub>sc</sub>	Short Circuit Withstand Time	V <sub>CC</sub> = 300 V, V <sub>GE</sub> = 15V @ T <sub>C</sub> = 100°C	10	--	--	us
Q <sub>g</sub>	Total Gate Charge	V <sub>CE</sub> = 300 V, I <sub>C</sub> = 20A, V <sub>GE</sub> = 15V	--	55	65	nC
Q <sub>ge</sub>	Gate-Emitter Charge		--	10	15	nC
Q <sub>gc</sub>	Gate-Collector Charge		--	20	30	nC

**Electrical Characteristics of DIODE @ Inverter & Brake**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 20\text{A}$	$T_C = 25^\circ\text{C}$	--	1.9	2.8	V
			$T_C = 100^\circ\text{C}$	--	2.0	--	
$t_{rr}$	Diode Reverse Recovery Time		$T_C = 25^\circ\text{C}$	--	75	150	ns
			$T_C = 100^\circ\text{C}$	--	110	--	
$I_{rr}$	Diode Peak Reverse Recovery Current	$I_F = 20\text{A}$ $di / dt = 40 \text{ A/us}$	$T_C = 25^\circ\text{C}$	--	1.3	2.6	A
			$T_C = 100^\circ\text{C}$	--	1.8	--	
$Q_{rr}$	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	--	50	195	nC
			$T_C = 100^\circ\text{C}$	--	100	--	

**Electrical Characteristics of DIODE @ Converter**  $T_C = 25^\circ\text{C}$  unless otherwise noted

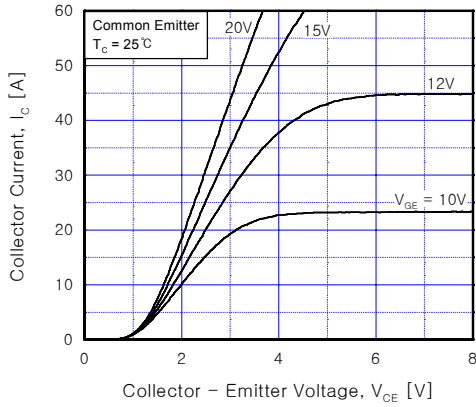
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 20\text{A}$	$T_C = 25^\circ\text{C}$	--	1.1	1.5	V
			$T_C = 100^\circ\text{C}$	--	1.0	--	
$I_{RRM}$	Repetitive Reverse Current	$V_R = V_{RRM}$	$T_C = 25^\circ\text{C}$	--	--	8	mA
			$T_C = 100^\circ\text{C}$	--	5	--	

**Thermal Characteristics**

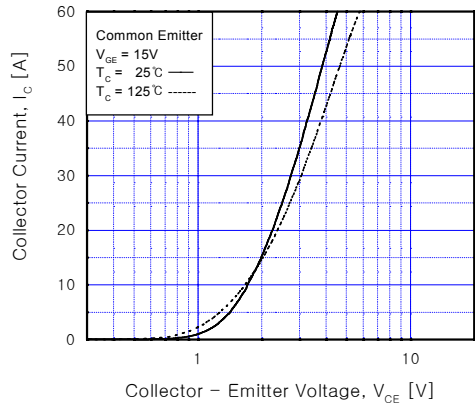
	Symbol	Parameter	Typ.	Max.	Units
Inverter	$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/6 Module)	--	1.4	$^\circ\text{C/W}$
	$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/6 Module)	--	2.3	$^\circ\text{C/W}$
Brake	$R_{\theta JC}$	Junction-to-Case (IGBT Part)	--	1.4	$^\circ\text{C/W}$
	$R_{\theta JC}$	Junction-to-Case (DIODE Part)	--	2.3	$^\circ\text{C/W}$
Converter	$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/6 Module)	--	1.5	$^\circ\text{C/W}$
Weight		Weight of Module	60	--	g

**NTC Thermistor Characteristics**

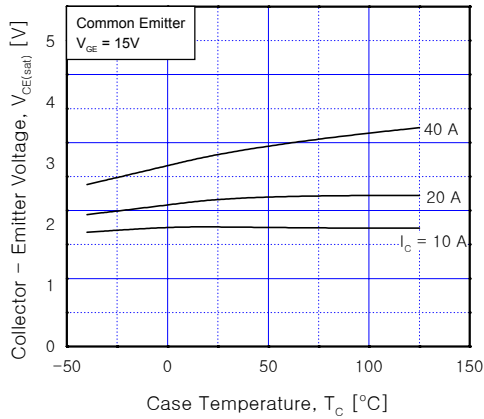
	Symbol	Parameter	Tol.	Typ.	Units
Thermistor	$R_{25}$	Rated Resistance @ $T_c = 25^\circ\text{C}$	+/- 5 %	4.7	$\text{K}\Omega$
	$R_{100}$	Rated Resistance @ $T_c = 100^\circ\text{C}$	+/- 5 %	0.39	$\text{K}\Omega$
	$B_{(25/100)}$	B - Value	+/- 3 %	3688	



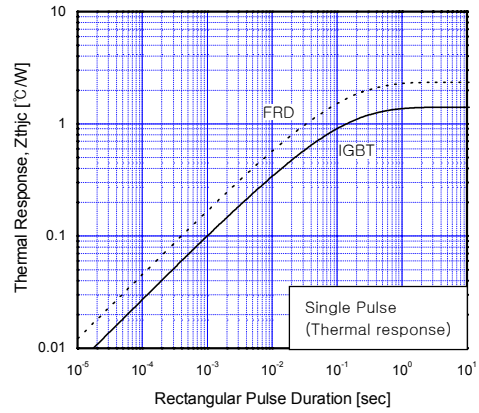
**Fig 1. Typical Output Characteristics**



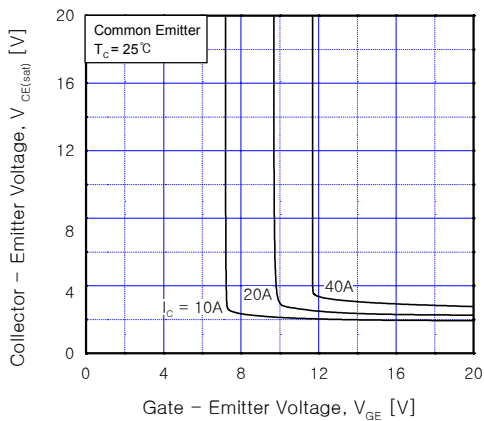
**Fig 2. Typical Saturation Voltage Characteristics**



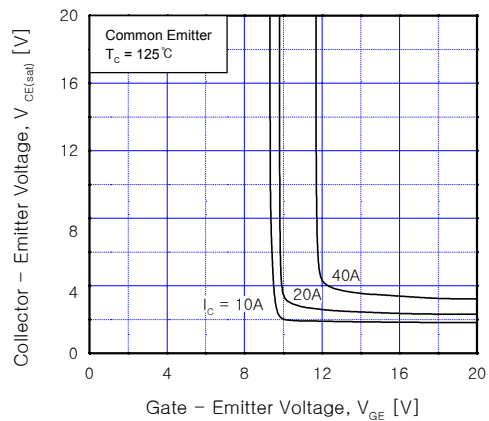
**Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level**



**Fig 4. Transient Thermal Impedance**



**Fig 5. Saturation Voltage vs. V\_GE**



**Fig 6. Saturation Voltage vs. V\_GE**

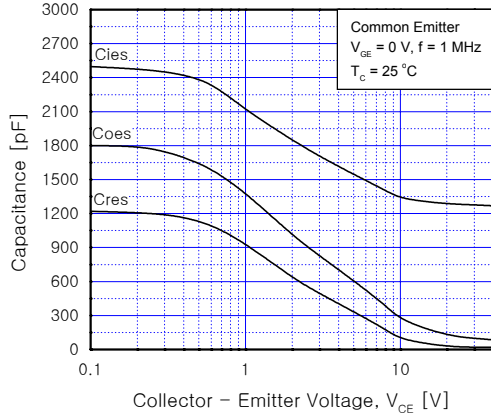


Fig 7. Capacitance Characteristics

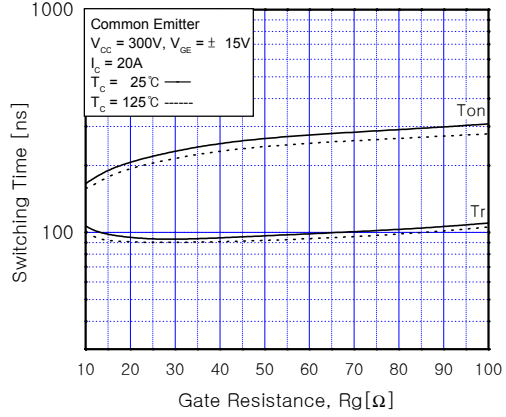


Fig 8. Turn-On Characteristics vs. Gate Resistance

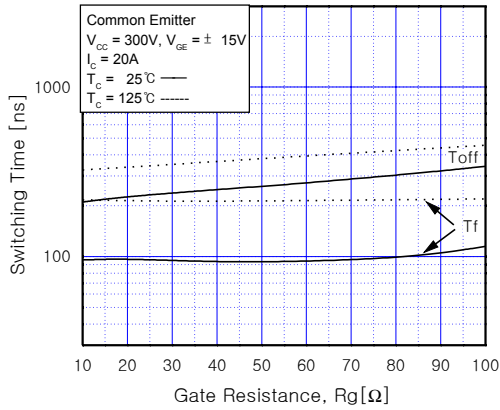


Fig 9. Turn-Off Characteristics vs. Gate Resistance

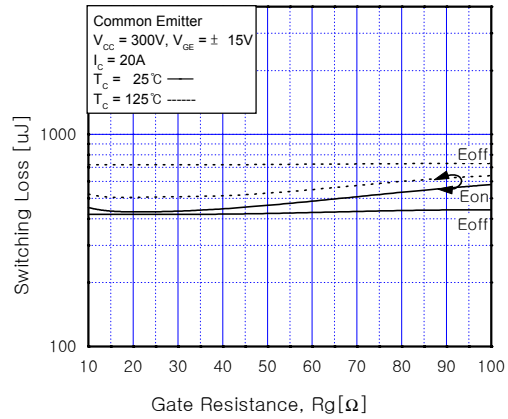


Fig 10. Switching Loss vs. Gate Resistance

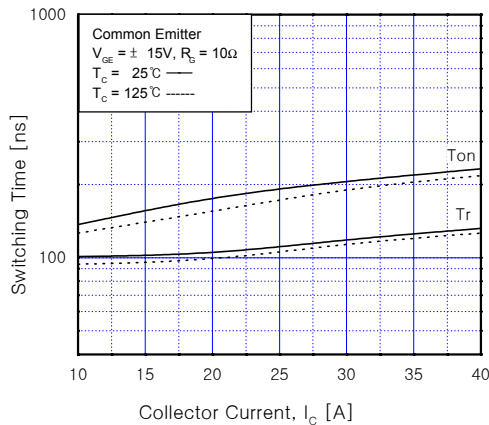


Fig 11. Turn-On Characteristics vs. Collector Current

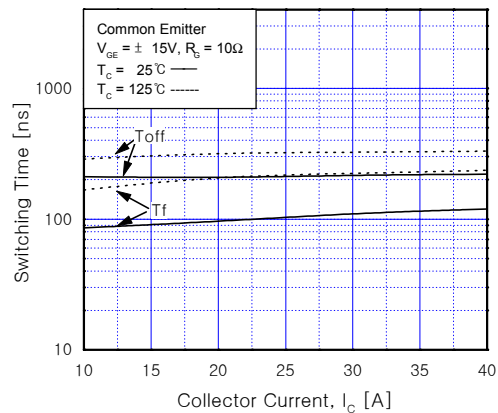
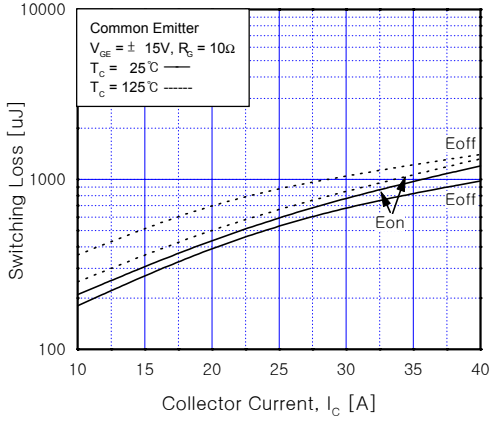
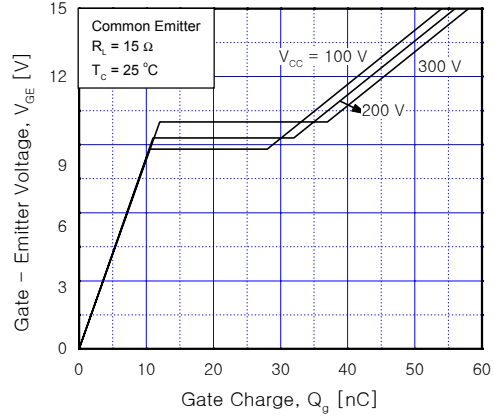


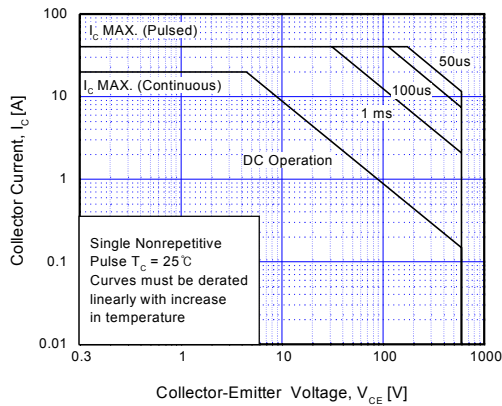
Fig 12. Turn-Off Characteristics vs. Collector Current



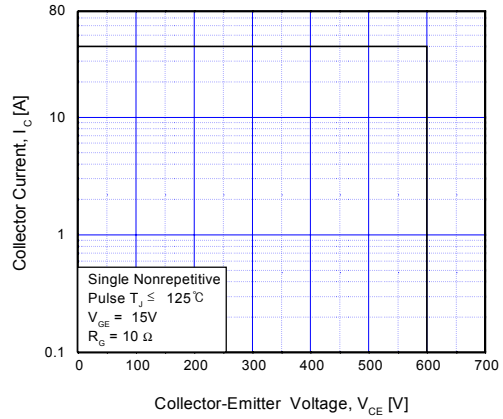
**Fig 13. Switching Loss vs. Collector Current**



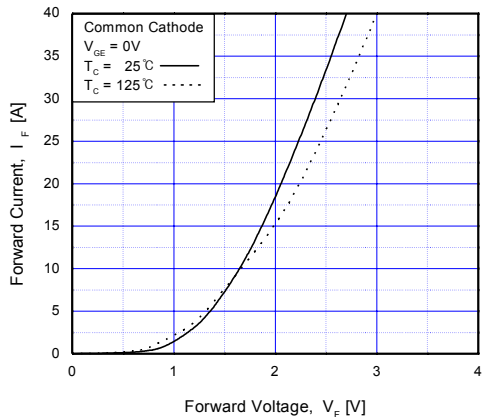
**Fig 14. Gate Charge Characteristics**



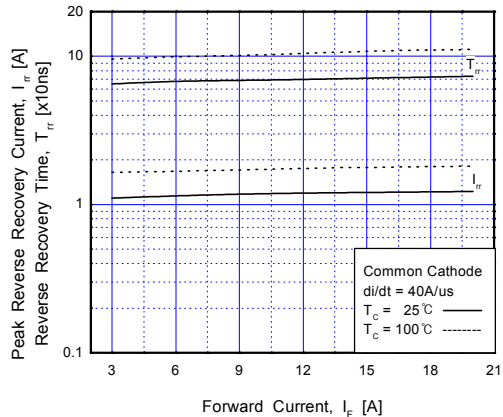
**Fig 15. SOA Characteristics**



**Fig 16. RBSOA Characteristics**



**Fig 17. Forward Characteristics**



**Fig 18. Reverse Recovery Characteristics**

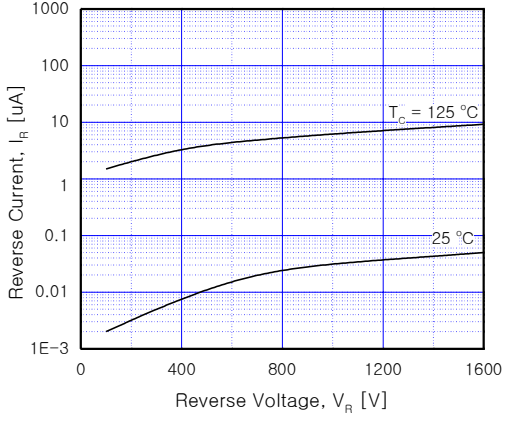


Fig 19. Rectifier( Converter ) Characteristics

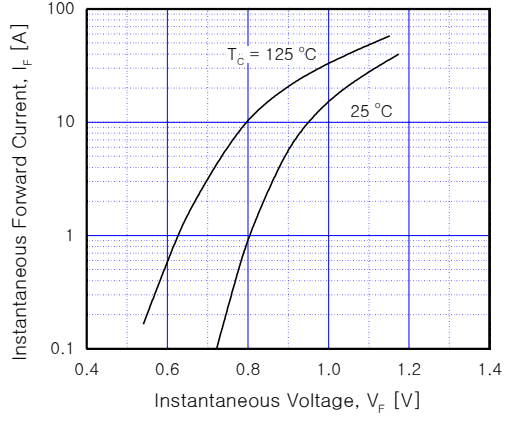


Fig 20. Rectifier( Converter ) Characteristics

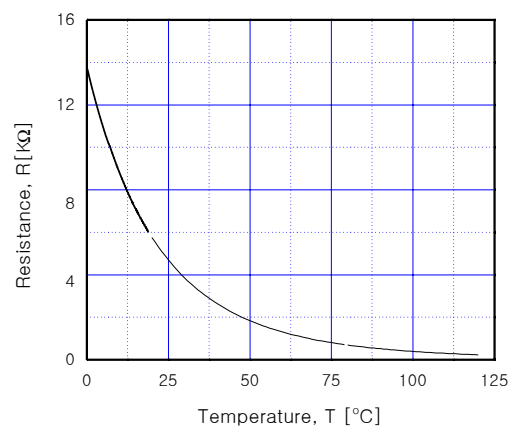


Fig 21. NTC Characteristics

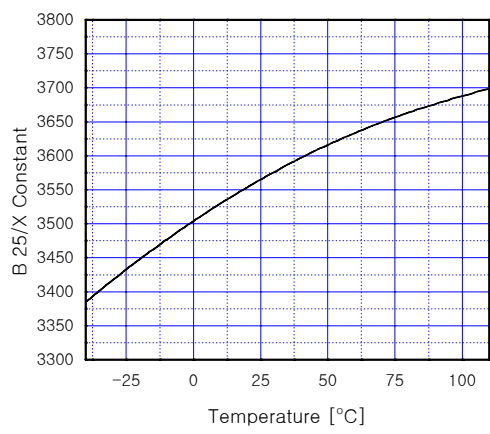
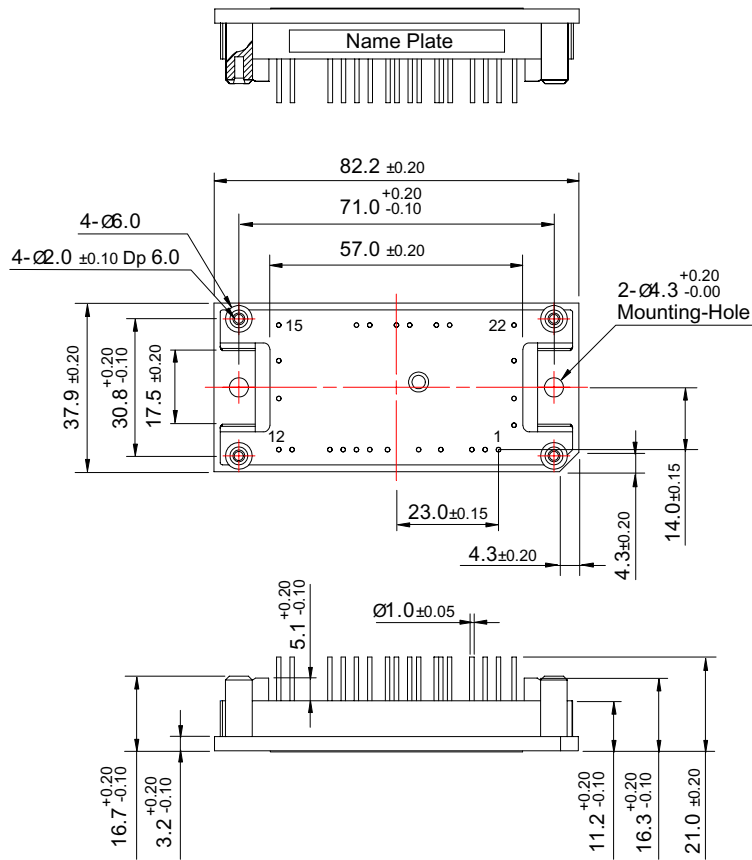


Fig 22. NTC Characteristics

# Package Dimension

## 25PM-AA

FMS7G20US60



### - Pin Coordinate

Pin #No	Coordinate	
	x	y
1	0.0	0.0
2	-3.0	0.0
3	-6.0	0.0
4	-13.0	0.0
5	-18.0	0.0
6	-25.0	0.0
7	-29.0	0.0
8	-32.0	0.0
9	-35.0	0.0
10	-38.0	0.0
11	-46.5	0.0
12	-49.5	0.0
13	-49.5	11.5
14	-49.5	20.0
15	-49.5	28.0
16	-32.0	28.0
17	-29.0	28.0
18	-23.0	28.0
19	-20.0	28.0
20	-14.0	28.0
21	-11.0	28.0
22	3.5	28.0
23	3.5	20.0
24	3.5	11.5
25	3.5	5.5

\* datum pin : #1

\* Pin Tilt : ±0.15

Dimensions in Millimeters



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Bottomless™	FAST®	LittleFET™	Power247™	SuperSOT™-3
CoolFET™	FAST <sup>r</sup> ™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic®
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I <sup>2</sup> C™	OCX™	RapidConfigure™	UHC™
Across the board. Around the world.™		OCXPro™	RapidConnect™	UltraFET®
The Power Franchise™		OPTOLOGIC®	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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